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CLAIMS

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What is claimed is:

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1. A method for characterizing an integrated circuit substrate, comprising:

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obtaining a substrate doping profile, the substrate doping profile including a

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net doping level for each one of a plurality of depths within the integrated circuit

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substrate;

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vertically discretizing the substrate doping profile to form a vertically

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discretized substrate doping profile; and

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associating the vertically discretized doping profile with an access key, the

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access key comprising a region name and a cross-section name.